

PSMN7R0-100PS

N-channel 100V 6.8 mΩ standard level MOSFET in TO220.

17 October 2013 Product data sheet

1. General description

Standard level N-channel MOSFET in TO220 package qualified to 175C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

2. Features and benefits

- High efficiency due to low switching and conduction losses
- · Improved dynamic avalanche performance
- Suitable for standard level gate drive

3. Applications

- DC-to-DC converters
- Load switching
- Motor control
- Server power supplies

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	100	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 1</u>	[1]	-	-	100	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	269	W
T _j	junction temperature			-55	-	175	°C
Static chara	acteristics		'		'		
R_{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 100 °C;$ Fig. 12		-	-	12	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ °C};$ Fig. 13		-	5.4	6.8	mΩ
Dynamic ch	naracteristics						
Q_{GD}	gate-drain charge	V_{GS} = 10 V; I_D = 25 A; V_{DS} = 50 V; - 36 Fig. 15; Fig. 14		-	nC		
Q _{G(tot)}	total gate charge	V _{GS} = 10 V; I _D = 25 A; V _{DS} = 50 V; Fig. 14; Fig. 15		-	125	-	nC



Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Avalanche rug	gedness					
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 100 A; V_{sup} = 100 V; unclamped; R_{GS} = 50 Ω	-	-	316	mJ

[1] Continuous current is limited by package

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D I
2	D	drain	704	
3	S	source		G—UNA
mb	D	mounting base; connected to drain		mbb076 S
			TO-220AB (SOT78)	

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PSMN7R0-100PS	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78			

7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN7R0-100PS	PSMN7R0-100PS

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	100	V
V_{DGR}	drain-gate voltage	$T_j \le 175 ^{\circ}\text{C}; T_j \ge 25 ^{\circ}\text{C}; R_{GS} = 20 \text{k}\Omega$		-	100	V
V_{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 1</u>		-	85	Α
		V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 1</u>	[1]	-	100	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 \text{ °C}$; Fig. 3		-	475	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	269	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T _{sld(M)}	peak soldering temperature			-	260	°C
Source-dra	in diode			1		
Is	source current	T _{mb} = 25 °C	[1]	-	100	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	475	Α
Avalanche	ruggedness		-	1		
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 100 A; V_{sup} = 100 V; unclamped; R_{GS} = 50 Ω		-	316	mJ

^[1] Continuous current is limited by package

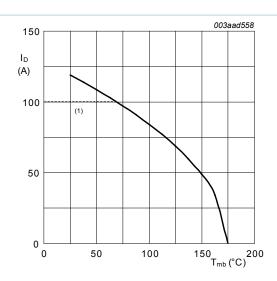


Fig. 1. Continuous drain current as a function of mounting base temperature

 $V_{GS} \ge 10 \text{ V}$; (1) capped at 100 A due to package.

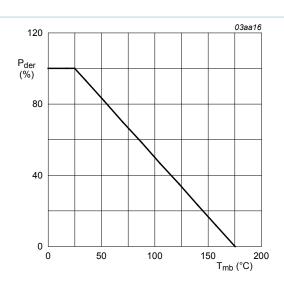


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

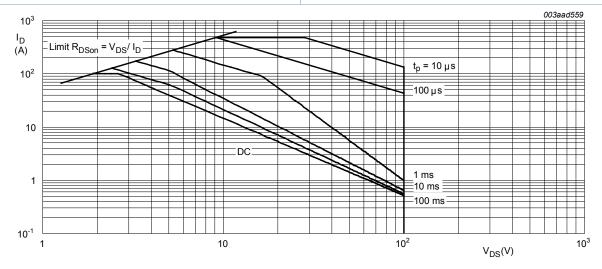


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

 $T_{mb} = 25 \,^{\circ}C; I_{DM}$ is single pulse

9. Thermal characteristics

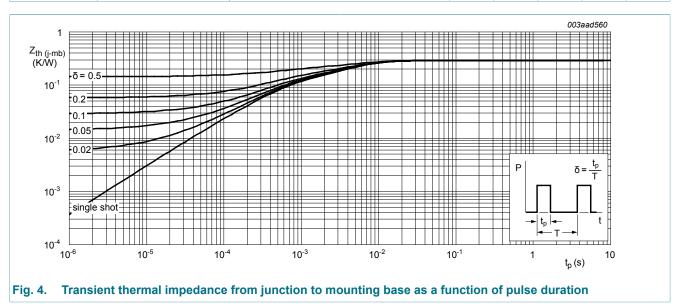
Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 4	-	0.3	0.56	K/W

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	vertical in free air	-	60	-	K/W



10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
Static characteristics							
V _{(BR)DSS}	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 ^{\circ}\text{C}$	90	-	-	V	
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	100	-	-	V	
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 175 °C; Fig. 10	1	-	-	V	
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; Fig. 11; Fig. 10	2	3	4	V	
	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = -55 °C; Fig. 10	-	-	4.6	V		
I _{DSS}	drain leakage current	V _{DS} = 100 V; V _{GS} = 0 V; T _j = 125 °C	-	-	150	μA	
		V _{DS} = 100 V; V _{GS} = 0 V; T _j = 25 °C	-	0.08	5	μA	
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	10	100	nA	
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	10	100	nA	
R _{DSon} drain-source on-st resistance	drain-source on-state resistance	V_{GS} = 10 V; I_D = 15 A; T_j = 100 °C; Fig. 12	-	-	12	mΩ	
		V_{GS} = 10 V; I_D = 15 A; T_j = 175 °C; Fig. 12	-	15	19	mΩ	

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C; Fig. 13	-	5.4	6.8	mΩ
R_G	internal gate resistance (AC)	f = 1 MHz	-	0.74	-	Ω
Dynamic ch	naracteristics		,			
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 50 V; V _{GS} = 10 V; Fig. 14; Fig. 15	-	125	-	nC
		I _D = 0 A; V _{DS} = 0 V; V _{GS} = 10 V	-	100	-	nC
Q_{GS}	gate-source charge	I _D = 25 A; V _{DS} = 50 V; V _{GS} = 10 V; Fig. 15; Fig. 14	-	28	-	nC
Q _{GS(th)}	pre-threshold gate- source charge	I _D = 25 A; V _{DS} = 50 V; V _{GS} = 10 V; Fig. 15	-	19.4	-	nC
Q _{GS(th-pl)}	post-threshold gate- source charge		-	9	-	nC
Q_{GD}	gate-drain charge	I _D = 25 A; V _{DS} = 50 V; V _{GS} = 10 V; Fig. 15; Fig. 14	-	36	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	V _{DS} = 50 V; <u>Fig. 15</u> ; <u>Fig. 14</u>	-	4.3	-	V
C _{iss}	input capacitance	V _{DS} = 50 V; V _{GS} = 0 V; f = 1 MHz;	-	6686	-	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 16</u>	-	438	-	pF
C _{rss}	reverse transfer capacitance		-	272	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 50 V; R_L = 2 Ω ; V_{GS} = 10 V;	-	34.6	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \Omega; T_j = 25 °C$	-	45.6	-	ns
t _{d(off)}	turn-off delay time		-	103.9	-	ns
t _f	fall time		-	49.5	-	ns
Source-dra	in diode		I	<u> </u>	1	
V _{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 17$	-	0.8	1.2	V
t _{rr}	reverse recovery time	I _S = 25 A; dI _S /dt = 100 A/μs; V _{GS} = 0 V;	-	64	-	ns
Q _r	recovered charge	V _{DS} = 50 V	-	167	-	nC

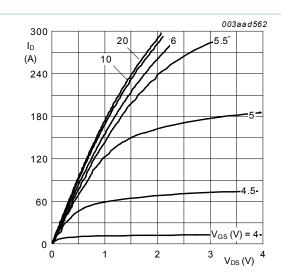


Fig. 5. Output characteristics: drain current as a function of drain-source voltage; typical values



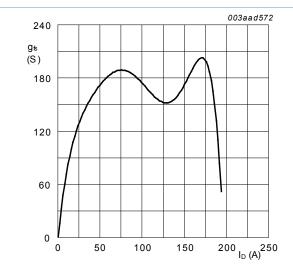


Fig. 7. Forward transconductance as a function of drain current; typical values

$$T_j = 25 \,^{\circ}C; V_{DS} = 15 \, V$$

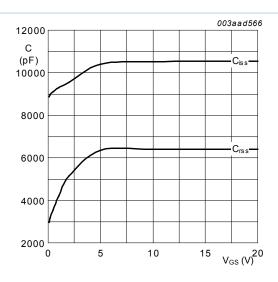


Fig. 6. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

$$V_{DS} = 0V; f = 1MHz$$

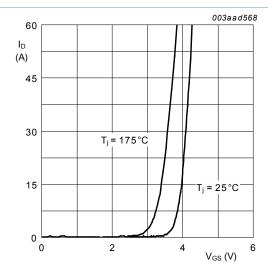


Fig. 8. Transfer characteristics: drain current as a function of gate-source voltage; typical values

$$V_{DS} > I_D \times R_{DSon}$$

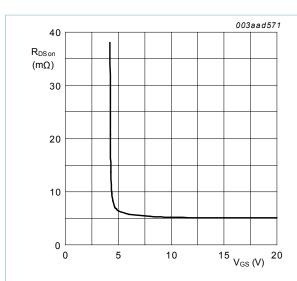


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25 \,^{\circ}C; I_D = 15A$$

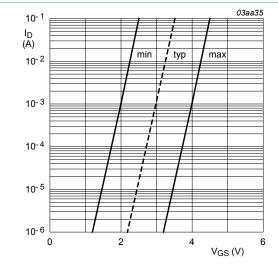


Fig. 11. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25 \,^{\circ}C; V_{DS} = 5V$$

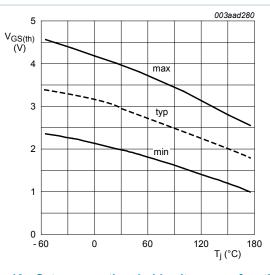


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1 \text{ mA}; \ V_{DS} = V_{GS}$$

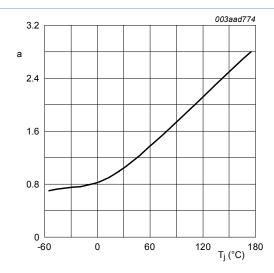


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25 \, ^{\circ}\text{C})}}$$

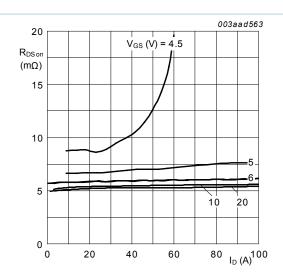
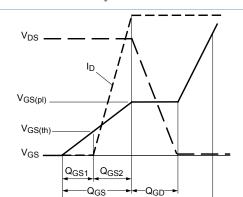


Fig. 13. Drain-source on-state resistance as a function of drain current; typical values

 $T_i = 25 \,^{\circ}C$



QG(tot)

003aaa508

Fig. 15. Gate charge waveform definitions

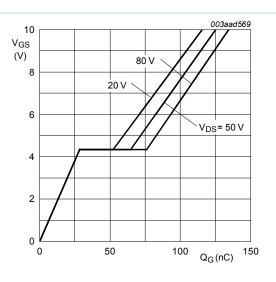


Fig. 14. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25\,^{\circ}C; I_D = 25A$$

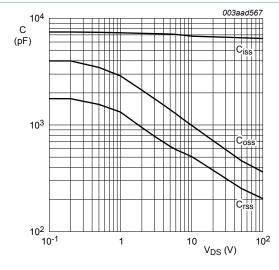


Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = \mathbf{0} V; f = \mathbf{1} M Hz$$

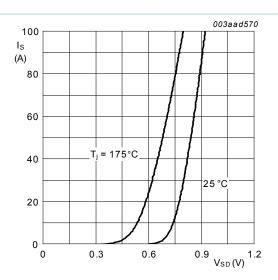
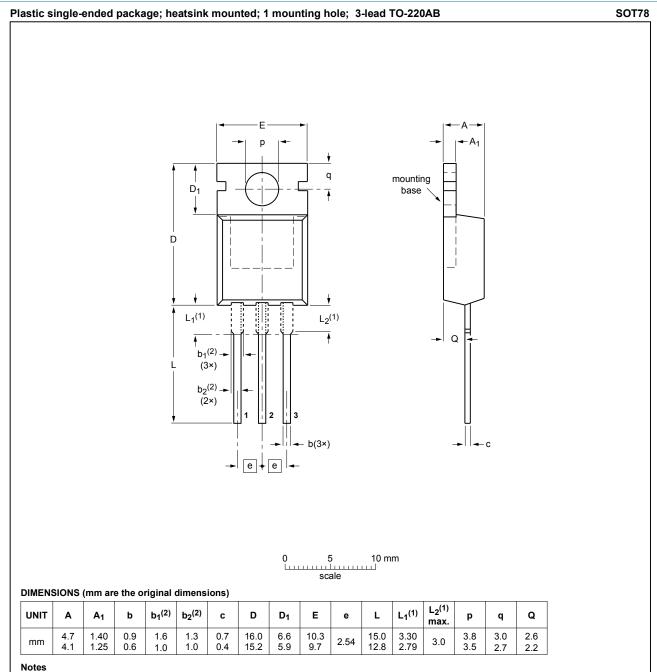


Fig. 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$$V_{GS} = 0 V$$

11. Package outline



- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE		REFERENCES				ISSUE DATE
VERSION	IEC	JEDEC	JEITA		PROJECTION	
SOT78		3-lead TO-220AB	SC-46			08-04-23 08-06-13

Fig. 18. Package outline TO-220AB (SOT78)

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